L Number	Hits	Search Text	DB	Time stamp
-	3269	waveguide.ti.	USPAT	2003/06/20 17:28
-	214	(waveguide and (form$5 or fabricat$3)).ti.	USPAT	2003/06/10 12:26
-	59	(waveguides and (form$5 or fabricat$3)).ti.	USPAT	2003/06/10 13:23
-	1	(wave-guide and (form$5 or fabricat$3)).ti.	USPAT	2003/06/10 12:21
-	455	(216/24).CCLS.	USPAT	2003/06/10 12:41
-	53	((216/24).CCLS.) and (waveguide or waveguides).ti.	USPAT	2003/06/10 12:44
-	221	(438/31).CCLS.	USPAT	2003/06/10 12:49
-	123	(65/385).CCLS.	USPAT	2003/06/10 12:46
-	105	(65/386).CCLS.	USPAT	2003/06/18 14:33
-	172	(264/1.24).CCLS.	USPAT	2003/06/10 12:46
-	303	(438/29).CCLS.	USPAT	2003/06/10 12:47
-	1164	(385/123).CCLS.	USPAT	2003/06/10 12:50
-	483	(385/124).CCLS.	USPAT	2003/06/10 12:50
-	279	(385/125).CCLS.	USPAT	2003/06/10 12:50
-	358	(385/126).CCLS.	USPAT	2003/06/11 09:15
-	404	(385/127).CCLS.	USPAT	2003/06/10 12:52
-	426	(385/128).CCLS.	USPAT	2003/06/10 12:54
-	655	(385/129).CCLS.	USPAT	2003/06/11 12:55
-	720	(385/130).CCLS.	USPAT	2003/06/10 12:58
-	562	(385/131).CCLS.	USPAT	2003/06/11 12:59
-	446	(385/132).CCLS.	USPAT	2003/06/10 12:56
-	430	(385/142).CCLS.	USPAT	2003/06/10 12:57
-	240	(385/144).CCLS.	USPAT	2003/06/10 12:57
-	764	(385/141).CCLS.	USPAT	2003/06/10 12:57
-	260	(385/143).CCLS.	USPAT	2003/06/10 12:58
-	225	(385/146).CCLS.	USPAT	2003/06/10 12:58
-	270	((438/29).CCLS.) not ((438/31).CCLS.)	USPAT	2003/06/10 13:01
-	142	((216/24).CCLS.) and (waveguide or wave-guide or waveguides)	USPAT	2003/06/10 13:06
-	1	("6571037").PN.	USPAT	2003/06/10 13:27
-	95	waveguide and ((material or materials) same (silicon or silica) same (InP or GaInAsP) same (doped or glass))	USPAT	2003/06/10 15:08
-	33	waveguide and core and cladding and ((material or materials) same (silicon or silica) same (InP or GaInAsP) same (doped or glass))	USPAT	2003/06/11 10:08
-	18	(waveguide or waveguides).ti. and ((silicon or silica) same (InP or GaInAsP) same (doped))	USPAT	2003/06/10 14:54
-	8	(waveguide or waveguides).ti. and (InP or GaInAsP) same (doped adj (silica or glass))	USPAT	2003/06/10 14:55
-	54	waveguide and ((material or materials) same (silicon or silica) same (InP or GaInAsP) same (doped))	USPAT	2003/06/10 16:23
-	58	waveguide.ti. and (silicon with substrate) and ((doped or doping) adj silica)	USPAT	2003/06/10 16:26
-	358	(385/126).CCLS.	USPAT	2003/06/11 09:16
-	99	((385/126).CCLS.) and (silica near5 cladding)	USPAT	2003/06/11 09:18
-	447	((silica adj glass) with cladding)	USPAT	2003/06/11 09:34
-	8	(((silica adj glass) with cladding)) and (216/24).ccls	USPAT	2003/06/11 09:19
-	77	((silica adj glass) adj cladding)	USPAT	2003/06/11 09:40
-	1	((silica adj glass) adj cladding) and anneal$3	USPAT	2003/06/11 09:40
-	23	("3934061" | "4820655" | "5206925" | "5253319" | "5295205" | "5324678" | "5408569" | "5637187" | "5678935" | "5703978" | "5719973" | "5732179" | "5783468" | "5885881" | "5904491" | "5982973" | "6044192" | "6122429" | "6177290" | "6201918" | "6208792" | "6303393" | "6317444").PN.	USPAT	2003/06/11 09:55
-	399	(waveguide and core and cladding) not (fiber or fibre)	USPAT	2003/06/11 11:00

-	206	((waveguide and core and cladding) not (fiber or fibre)) and (silica or glass or quartz)	USPAT	2003/06/11 10:49
-	26	((waveguide and core and cladding) not (fiber or fibre)) and (silica adj glass)	USPAT	2003/06/11 10:27
-	10	((waveguide and core and cladding) not (fiber or fibre)) and ((silica adj glass) with cladding)	USPAT	2003/06/11 10:12
-	31	((waveguide and core and cladding) not (fiber or fibre)) and (silica or glass or quartz) and anneal$3	USPAT	2003/06/11 10:32
-	33	((waveguide and core and cladding) not (fiber or fibre)) and ((silica adj glass) or PSG or BPSG or silicate)	USPAT	2003/06/11 10:27
-	35	((waveguide and core and cladding) not (fiber or fibre)) and (silica or glass or quartz or polysilicon) and anneal$3	USPAT	2003/06/11 10:33
-	0	PSG with polusilicon and glass	USPAT	2003/06/11 10:33
-	398	PSG with polysilicon and glass	USPAT	2003/06/11 10:34
-	207	PSG with polysilicon with glass	USPAT	2003/06/11 10:34
-	20	((waveguide and core and cladding) not (fiber or fibre)) and fused adj silica	USPAT	2003/06/11 10:49
-	299	(waveguide and (fabrication or fabricating or forming or making or formation)).ti.	USPAT	2003/06/11 11:03
-	562	(385/131).CCLS.	USPAT	2003/06/11 13:01
-	446	(385/132).CCLS.	USPAT	2003/06/11 13:02
-	418	((385/131).CCLS.) not ((385/132).CCLS.)	USPAT	2003/06/18 11:29
-	221	(438/31).CCLS.	USPAT	2003/06/11 14:22
-	12	("4495412" | "4606602" | "4715672" | "4776087" | "4851025" | "4901329" | "5002352" | "5444805" | "5518965" | "5533156" | "5565693" | "5604835").PN.	USPAT	2003/06/11 15:15
-	295	waveguide.ti. and (buffer adj layer)	USPAT	2003/06/11 14:46
-	42	waveguide.ti. and (buffer adj layer) and (anneal or annealing)	USPAT	2003/06/11 14:46
-	448	(385/132).CCLS.	USPAT	2003/06/18 11:07
-	131	((385/132).CCLS.) and core and (clad or cladding) and (oxide or dioxide or silicon or "SiO.sub.2" or SiO2)	USPAT	2003/06/18 11:08
-	14	4652290.URPN.	USPAT	2003/06/18 11:19
-	327	waveguide.ti. and (channel or trench).clm.	USPAT	2003/06/18 11:23
-	8	("5054872" | "5136682" | "5142605" | "5165004" | "5170461" | "5282078" | "5291574" | "5352566").PN.	USPAT	2003/06/18 11:28
-	420	((385/131).CCLS.) not ((385/132).CCLS.)	USPAT	2003/06/18 11:48
-	142	((216/24).CCLS.) and (waveguide or ((wave or light) adj guide))	USPAT	2003/06/18 12:01
-	2	("4919749" | "5308442").PN.	USPAT	2003/06/18 11:55
-	0	5431775.URPN.	USPAT	2003/06/18 11:55
-	0	5431775.URPN.	USPAT	2003/06/18 11:55
-	5689	(waveguide or ((wave or light) adj guide)) and etch$3 and ((silicon adj (oxide or dioxide)) or "SiO.sub.2" or SiO2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 12:06
-	818	(waveguide or ((wave or light) adj guide)).ti. and etch$3 and ((silicon adj (oxide or dioxide)) or "SiO.sub.2" or SiO2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 12:15
-	157	((waveguide or ((wave or light) adj guide)).ti. and etch$3 and ((silicon adj (oxide or dioxide)) or "SiO.sub.2" or SiO2)) and core and clad$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 12:15
-	7	((waveguide or ((wave or light) adj guide)).ti. and etch$3 and ((silicon adj (oxide or dioxide)) or "SiO.sub.2" or SiO2)) and core and clad$3	JPO	2003/06/18 12:15

-	28	((waveguide or ((wave or light) adj guide)).ti. and etch$3 and ((silicon adj (oxide or dioxide)) or "SiO.sub.2" or SiO2))	JPO	2003/06/18 12:15
-	20	(waveguide or ((wave or light) adj guide)).ti. and silicon and (channel or trench)	EPO; JPO	2003/06/18 12:19
-	60	(Schottky and photodiode).ab.	EPO; JPO	2003/06/18 12:20
-	34	(Schottky and photodiode).ab.	USPAT; US-PGPUB	2003/06/18 12:21
-	123	(photodiode).ti. and silicon and (oxide or dioxide) and etch$3	USPAT; US-PGPUB	2003/06/18 12:22
-	44	(photodiode).ti. and silicon and (oxide or dioxide) and (etch$3 or remov$3).clm.	USPAT; US-PGPUB	2003/06/18 12:23
-	8	3980461.URPN.	USPAT	2003/06/18 14:28
-	11	("2035827" | "2053551" | "2054166" | "3278283" | "3455667" | "3455668" | "3542535" | "3647406" | "3771983" | "3879182" | "3926601").PN.	USPAT	2003/06/18 14:29
-	19370	(silicon adj (nitride and oxide)) and mask$3 and etch$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:39
-	1341	((silicon adj (nitride and oxide)) and mask$3 and etch$3).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 11:52
-	49	((silicon adj (nitride and oxide)) and (hard adj mask$3) and etch$3).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 11:52
-	556	((silicon adj (nitride and oxide)) and mask$3 and etch$3) and (waveguide or (light adj guide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 11:57
-	532	(((silicon adj (nitride and oxide)) and mask$3 and etch$3) and (waveguide or (light adj guide))) and (trench or groove or channel or cavity or via or opening or gap or void or ditch or street or trough or furrow)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:06
-	106	((((silicon adj (nitride and oxide)) and mask$3 and etch$3) and (waveguide or (light adj guide))) and (trench or groove or channel or cavity or via or opening or gap or void or ditch or street or trough or furrow)) and (core and clad$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:00
-	60	(silicon adj (nitride and oxide)) and mask$3 and etch$3 and (SOI or silicon-on-insulator) and etch-stop	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:31
-	55	(silicon adj (nitride and oxide)) and mask$3 and etch$3 and (SOI or silicon-on-insulator) and waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:31
-	1588	(silicon adj (nitride and oxide)) and (hard adj mask$3) and etch$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:41
-	40	(silicon adj (nitride and oxide)) and (hard adj mask$3) and (etch$3 with trench) and (waveguide or diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 14:59

–	634	(silicon adj (nitride and oxide)) and (hard adj mask$3) and (etch$3 with trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 12:45
–	46	(trench and waveguide$1).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 13:09
–	243	(trench and waveguide$1).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 13:09
–	1	1993-314383.NRAN.	DERWENT	2003/06/19 17:03
–	876	core and clad$4 and etch$3 and waveguide and silicon and (refractive adj index)	USPAT	2003/06/19 18:08
–	254	core and clad$4 and etch$3 and waveguide.ti. and silicon and (refractive adj index)	USPAT	2003/06/19 18:11
–	535	core and clad$4 and etch$3 and waveguide and dop$3 and silicon and (refractive adj index)	USPAT	2003/06/19 18:11
–	146	core and clad$4 and etch$3 and waveguide.ti. and dop$3 and silicon and (refractive adj index)	USPAT	2003/06/19 18:18
–	73	((first and second) adj clad$3) same (refractive adj index)	USPAT	2003/06/19 18:27
–	3	((top and bottom) adj clad$3) same (refractive adj index)	USPAT	2003/06/19 18:20
–	89	((clad$3) with (refractive adj index) with ((first and second) or (top and bottom))) and waveguide	USPAT	2003/06/19 18:29
–	11	waveguide and ((CMP or (chemical adj mechanical adj polishing)) same core)	USPAT	2003/06/20 16:36
–	2	waveguide and (trench with etch$3 with (silicon-on-insulator or SOI))	USPAT	2003/06/20 17:31
–	4	waveguide and (trench same etch$3 same (silicon-on-insulator or SOI))	USPAT	2003/06/20 17:33
–	398	(trench same etch$3 same (silicon-on-insulator or SOI))	USPAT	2003/06/20 17:34